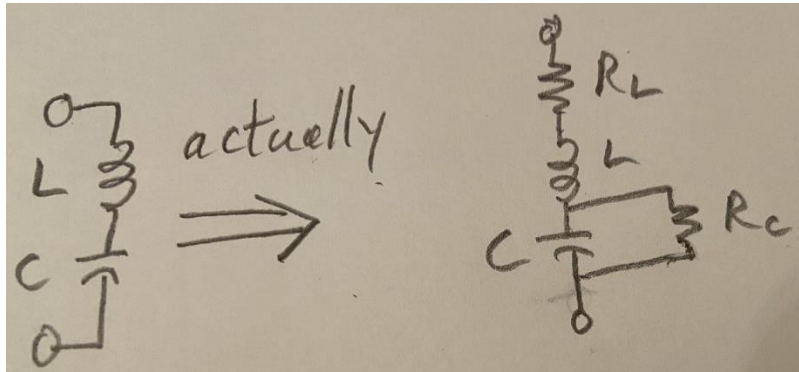


Damping

All physical systems are lossy or dissipative (i.e. they have energy loss mechanisms).

Circuit example:



R_L represents the resistance of the wire used to make L .

R_C represents the leakage path through C .

In mechanical systems, energy losses are modelled by a Damping Coefficient, c .

$$[c] = \text{Kg/s}$$

$$\text{Damping Force} \equiv F_D = cv = c \frac{dy}{dt} = c\dot{y}$$

In the macro world (our world), friction is often the most important mechanical energy loss mechanism.

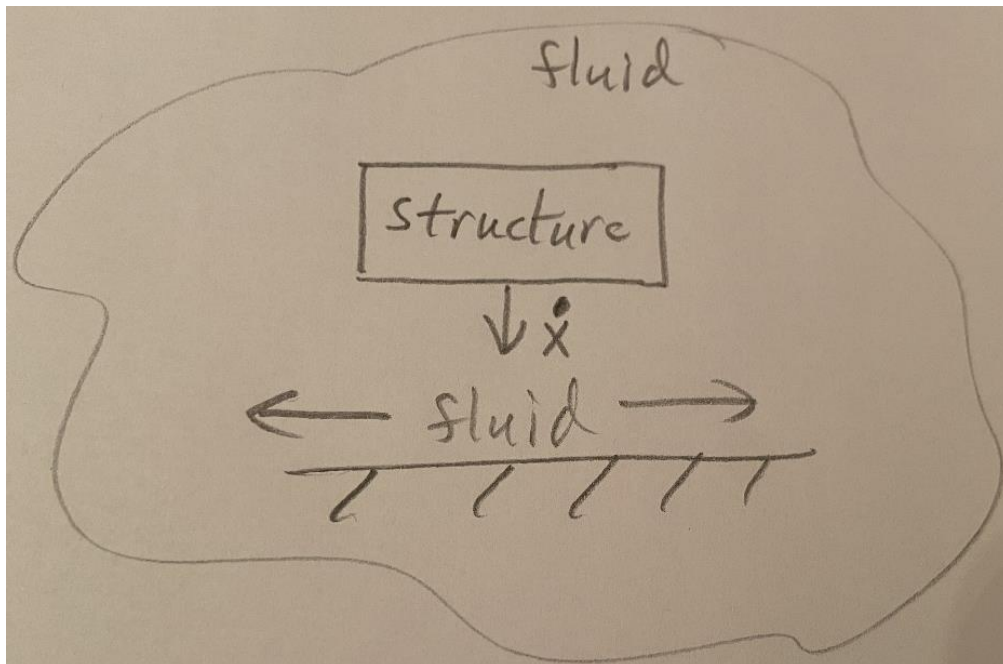
In the micro world, there are both internal and external energy loss mechanisms to consider:

Internal Sources

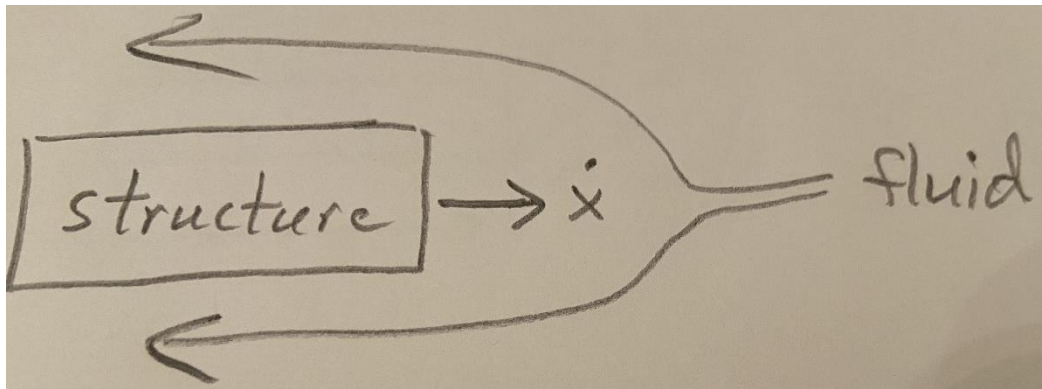
- 1) Thermoelastic Damping: an internal coupling of mechanical stress/strain and heat flow in a material. Some of the energy used to deform the beam gets converted to heat.

External Sources

- 1) Friction
- 2) Impact
- 3) Eddy current damping: a DC magnetic field in a moving conductor creates a drag force that resists that motion.
- 4) Interaction with a surrounding fluid: fluidic damping
 - a) Squeeze-Film Damping: from the compression of a surrounding fluid – the fluid is forced out by compression



- b. Shear-Resistance Damping: from a resistance to shearing of a fluid as an object moves through it



With microstructures, a gas is the fluid. Gases are compressible.

$$c = f(\text{geometry}, \mu), \text{ where } \mu \text{ is gas viscosity.}$$

For gas pressures $>$ few hundred Pa: μ is not proportional to P

$$1 \text{ atm} = 760 \text{ Torr} = 101,325 \text{ Pa}$$

$$\rightarrow 200 \text{ Pa} \approx 1.5 \text{ Torr} \quad [\text{Mars' atmosphere} \approx 5.03 \text{ Torr}]$$

For pressures $<$ few hundred Pa: $\mu \propto P \rightarrow c \propto P$

$$10^{-3} \text{ Torr} (0.133 \text{ Pa}) \sim \text{low vacuum}$$

$$10^{-7} \text{ Torr} (1.33 \times 10^{-5} \text{ Pa}) \sim \text{high vacuum}$$

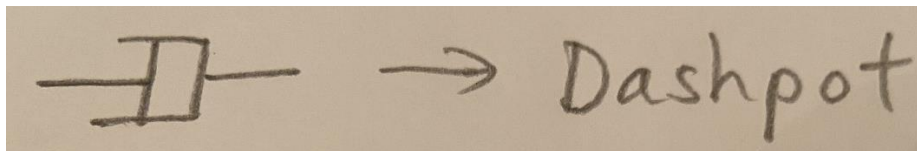
When a MEMS device is not packaged in a vacuum environment:
fluidic damping \gg thermoelastic damping

Therefore, MEMS devices are often sealed in a low pressure inert or dry gas to set the damping to a desired range.

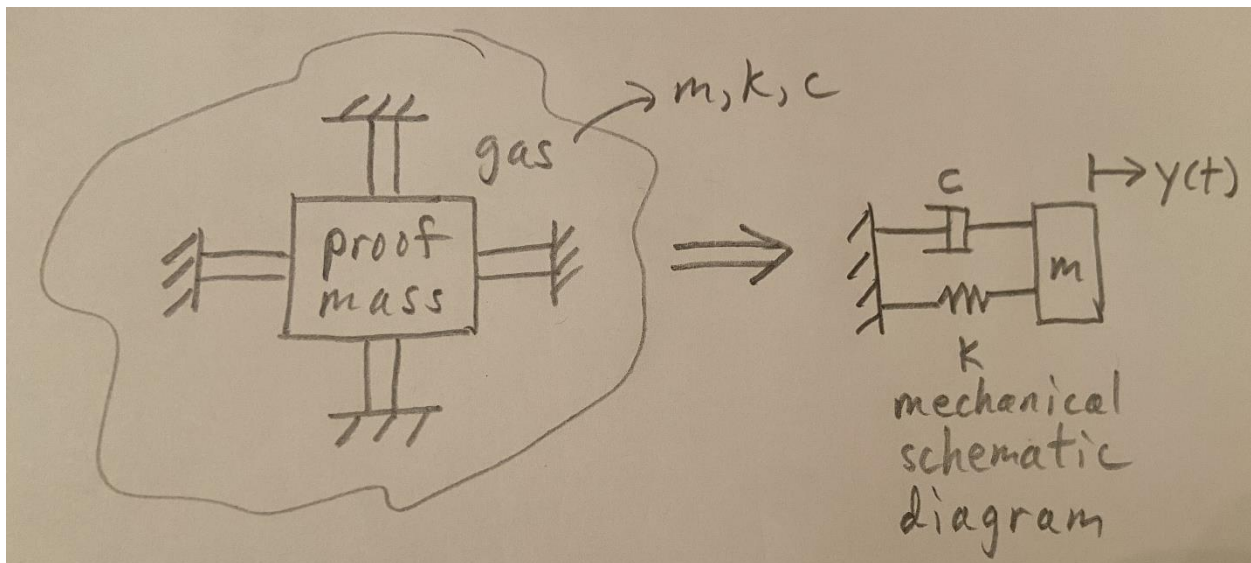
“Desired Range” → c varies with temperature.
→ all packages leak: can use “getters” to trap small amounts of gases leaking into the package.

A getter is a material the binds residual gas (typically only certain gases) in a vacuum sealed package or a vacuum system in attempt to maintain a high vacuum environment. The getter is often activated by heat after package assembly.

Schematic Symbol for Damping: c



Therefore, our spring-mass-damper system becomes:



System Dynamics with Damping Included

$F_I + F_D + F_S = 0 \rightarrow m\ddot{x} + c\dot{x} + kx = 0$ Note: using x or y for displacement changes nothing.

Let's rewrite the equation as: $\ddot{x} + \frac{c}{m}\dot{x} + \frac{k}{m}x = 0$

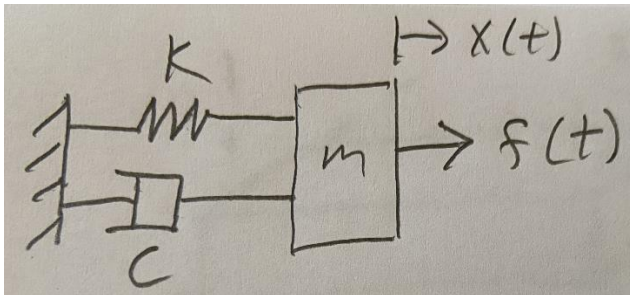
Use $\omega_n = \sqrt{\frac{k}{m}} \equiv$ natural frequency

$\zeta \equiv$ damping ratio and $Q \equiv$ mechanical quality factor, where:

$$\frac{c}{m} = 2\zeta\omega_n = \frac{\omega_n}{Q} \rightarrow Q = \frac{1}{2\zeta} : \text{High } Q = \text{low damping}$$

$\therefore \ddot{x} + 2\zeta\omega_n\dot{x} + \omega_n^2x = 0$: another form of our system differential EQ.

Let's apply an external force, $f(t)$, to our MEMS device:



Now: $m\ddot{x} + c\dot{x} + kx = f(t)$

Using Laplace transforms: $ms^2X(s) + csX(s) + kX(s) = F(s)$

Or: $X(s)[ms^2 + cs + k] = F(s)$

We can define a mechanical transfer function: $T(s)$, where:

$$T(s) = \frac{X(s)}{F(s)} = \frac{1}{ms^2 + cs + k} = \frac{1/m}{s^2 + 2\zeta\omega_n s + \omega_n^2}$$

So what does this mean?

At DC, $f(t)$ would be a constant force producing a linear acceleration of the proof mass.

At AC, $f(t)$ is a sinusoidal force causing the proof mass to oscillate back and forth at a frequency, f , (i.e. it vibrates).

$T(s)$ is a second order function with a low pass frequency response.

Therefore, our spring-mass-damper is a mechanical 2nd order low pass filter that filters mechanical vibrations.

If our device has very low damping (high Q), which is very common for MEMS devices, it will have a mechanical gain near f_n (small force: large proof mass motion in the vicinity of f_n).

Reasonable Answers with MEMS Problems

Always think about your numerical answers to see if they are reasonable.

1) Reasonable mass

Consider a “large” Si chip for a MEMS device: 1 cm x 1 cm x 500 μm .

Since $\delta_{\text{Si}} = 2.3 \text{ g/cm}^3$, the entire chip can only have a mass of 115 mg.

Mass of the proof mass \ll 115 mg.

2) Reasonable natural frequency

$\omega_n = 2\pi f_n \rightarrow f_n$ is usually in the audio range: 20 Hz to 20 kHz.

3) Reasonable proof mass displacements

Reasonable proof mass displacements \ll chip width for lateral motion or \ll chip thickness for vertical motion: 0.1 to 10 μm is reasonable.

Note: displacements cannot exceed gap distances!

4) Reasonable capacitance values

Reasonable MEMS capacitors \sim 1 pF: 10 pF \rightarrow a really large MEMS cap

Note: MEMS associated capacitances can be much smaller than this, even less than 1 fF (femto Farad: 1×10^{-15} F), particularly if you are considering a change in capacitance.

5) Reasonable voltages and currents

Reasonable voltages can be up to a few 100 V.

What is the approximated current from continuously fully charging and discharging a 10 pF MEMS capacitor with 100 V at 20 kHz:

$$\text{Let } I = \frac{dQ}{dt} \approx fCV = 20,000 * 10 \times 10^{-12} * 100 = 20 \mu\text{A} \ll 1\text{A}.$$

Example unreasonable answers to MEMS problems:

1 m proof mass displacement

10 kg proof mass

V = 10,000 V

I = 10 A

$F_n = 2$ MHz

C = 10 μF